

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Super Trench technology
- ☒ Extremely Low $R_{DS(ON)}$ and Q_g
- ☒ T_J 175°C
- ☒ MSL1

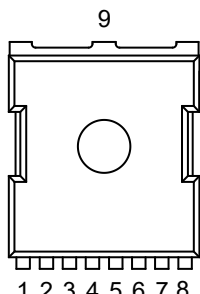
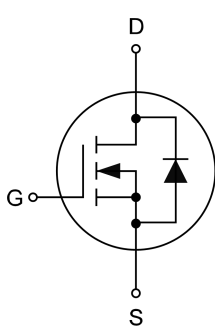
1.2 Applications

- ☒ Motor control and drive
- ☒ High power inverter system
- ☒ BMS
- ☒ UPS

1.3 Quick reference

- ☒ $BV \geq 250\text{ V}$
- ☒ $P_D \leq 375\text{ W}$
- ☒ $I_D \leq 100\text{ A}$
- ☒ $R_{DS(ON)} \leq 18\text{ m}\Omega @ V_{GS} = 10\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate	 Top View TOLL-8L	
2,3,4,5,6,7,8	Source		
9	Drain		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	250	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
I_D	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	100	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	70	A
I_{DM}^*	Drain Current (Pulsed)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	400	A
P_D	Drain Power Dissipation	$T_C=25^{\circ}\text{C}$	-	375	W
I_S	Continuous-Source Current	$T_C=25^{\circ}\text{C}$	-	100	A
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	175	$^{\circ}\text{C}$
E_{AS}	Single Pulsed Avalanche Energy	$V_{DD}=50\text{ V}, L=0.3\text{ mH}$	-	396	mJ
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient		-	62.5	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case		-	0.4	$^{\circ}\text{C/W}$

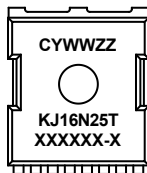
Notes:

* Surface mounted on 1 in² pad area, $t \leq 10\text{ sec.}$

** Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

*** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ16N25T	

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity (pcs)
KJ16N25T	TOLL-8L	13"	24 mm	2000

Note: KUAIJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

6. Electrical Characteristics (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	250	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	2.0	-	4.0	V
I _{DSS}	Drain Leakage Current	V _{DS} =250 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{DS} =0 V, V _{GS} =±20 V	-	-	±100	nA
R _{DS(ON)}	On-State Resistance	V _{GS} =10 V, I _{DS} =50 A	-	16	18	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5 V, I _{DS} =50 A	-	90	-	S
R _G	Gate resistance	V _{GS} =V _{DS} =0 V, Frequency=1 MHz	-	3.5	-	Ω
Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0 V, I _{SD} =50 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} =0 V, I _{SD} =50 A, dI _{SD} /dt=100 A/μs	-	165	-	ns
Q _{rr}	Reverse Recovery Charge		-	1060	-	nC
Dynamic Characteristics						
C _{iSS}	Input Capacitance	V _{DS} =125 V, V _{GS} =0 V, Frequency=1 MHz	-	4310	-	pF
C _{oSS}	Output Capacitance		-	364	-	
C _{rSS}	Reverse Transfer Capacitance		-	50	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =125 V, V _{GEN} =10 V, R _G =2.7 Ω, I _{DS} =50 A	-	15	-	ns
t _r	Turn-on Rise Time		-	46	-	
t _{d(off)}	Turn-off Delay Time		-	50	-	
t _f	Turn-off Fall Time		-	30	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =125 V, V _{GS} =10 V, I _{DS} =50 A	-	65	-	nC
Q _{gs}	Gate-Source Charge		-	29	-	
Q _{gd}	Gate-Drain Charge		-	9	-	

7. Typical Characteristics

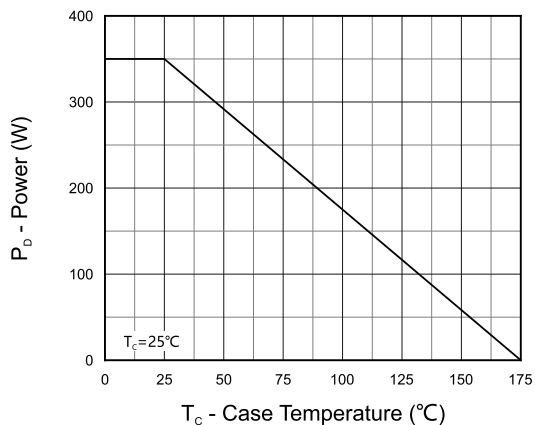


Figure 1. Power Capability

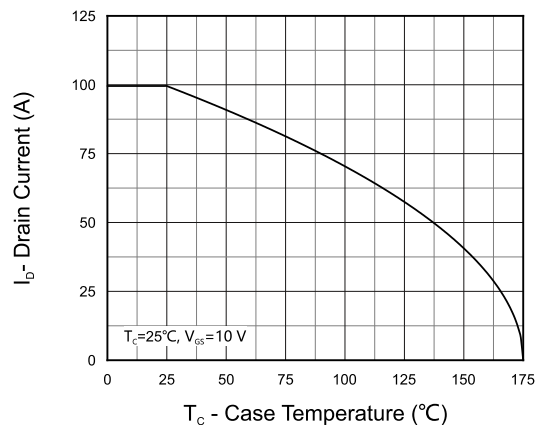


Figure 2. Current Capability

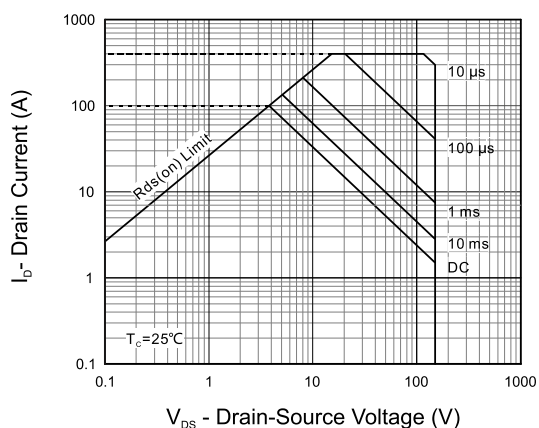


Figure 3. Safe Operation Area

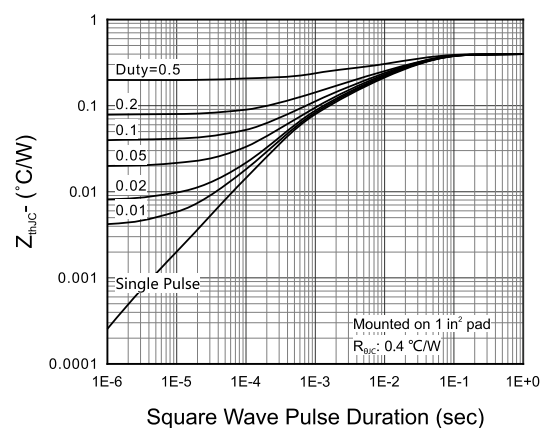


Figure 4. Transient Thermal Impedance

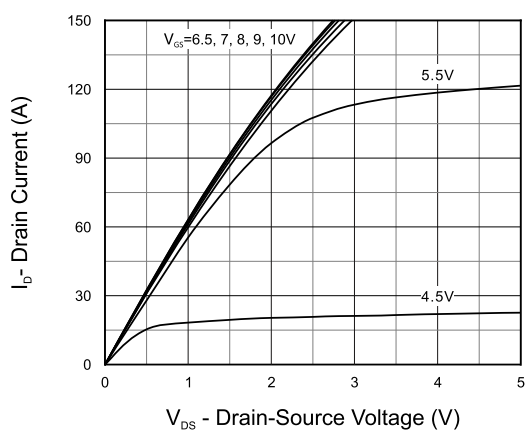


Figure 5. Output Characteristics

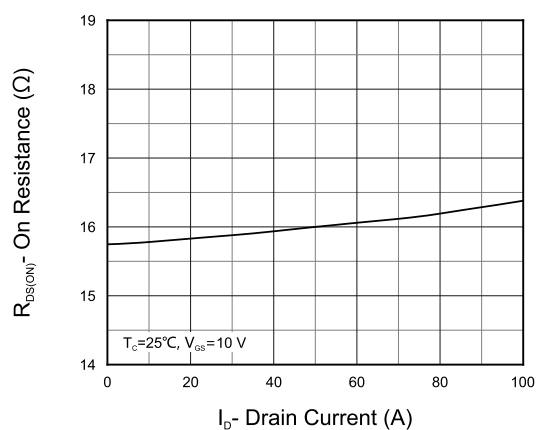


Figure 6. $R_{DS(ON)}$ vs. I_D

7. Typical Characteristics (cont.)

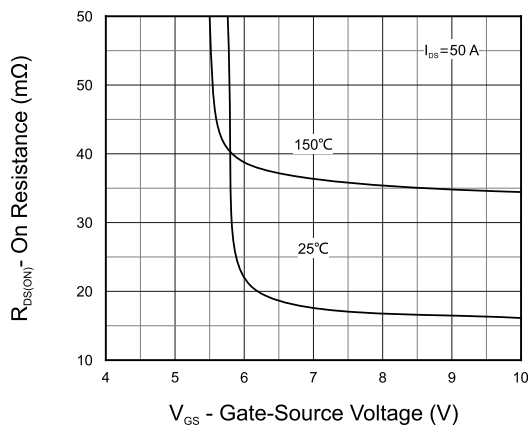


Figure 7. Transfer Characteristics

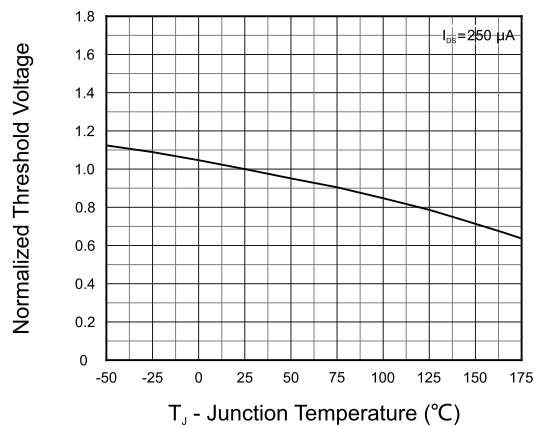


Figure 8. Normalized Threshold Voltage

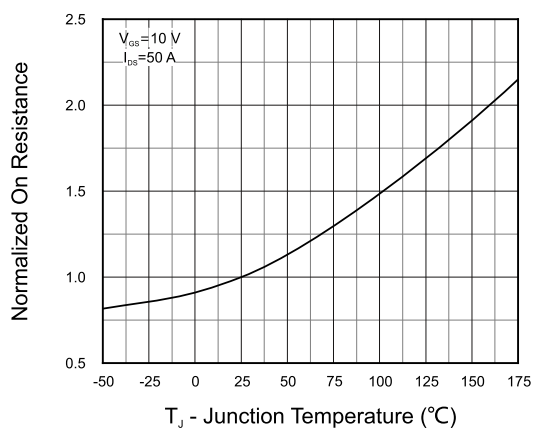


Figure 9. Normalized On Resistance

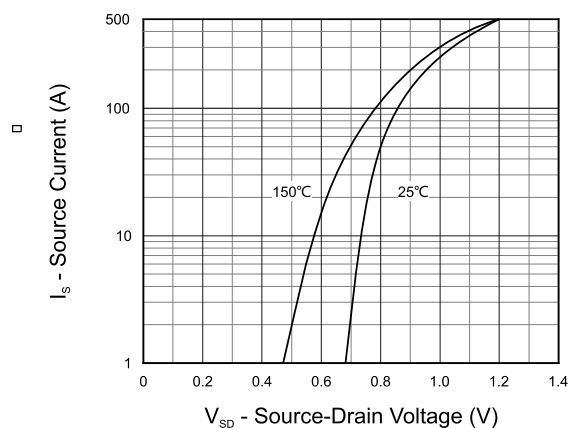


Figure 10. Diode Forward Current

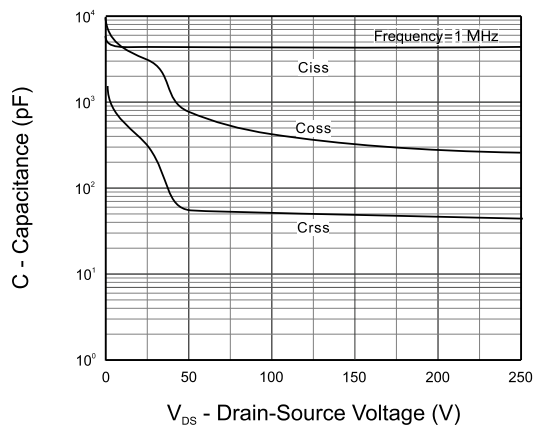


Figure 11. Capacitance

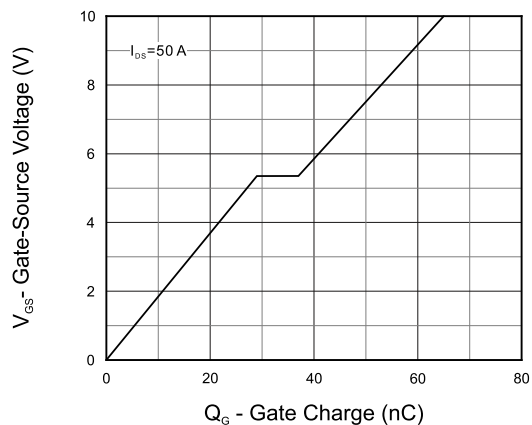
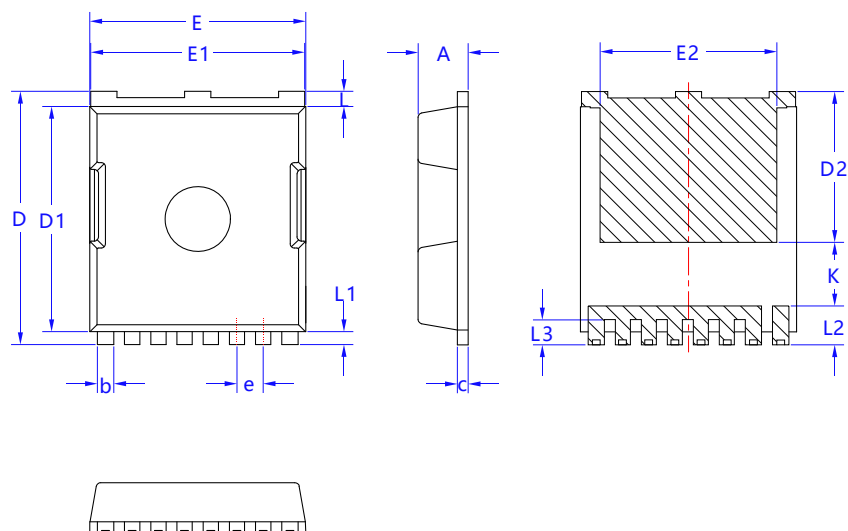


Figure 12. Gate Charge

8. Package Dimensions

TOLL-8L package



Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
A	2.20	2.30	2.40
b	0.60	0.70	0.90
c	0.40	0.50	0.60
D	11.48	11.68	11.88
D1	10.28	10.38	10.55
D2	6.85	6.95	7.05
E	9.80	9.90	10.0
E1	9.70	9.80	9.90
E2	8.00	8.10	8.20
e	1.20 BSC		
L	0.60 TYPE		
L1	0.60 TYPE		
L2	1.60	1.80	2.10
L3	1.00	1.15	1.30
K	2.90 TYPE		